

# GP1S96J0000F

Gap: 1mm, Slit: 0.3mm **Phototransistor Output, Compact Transmissive Photointerrupter** 

#### **■** Description

GP1S96J0000F is a compact-package, phototransistor output, transmissive photointerrupter, with opposing emitter and detector in a molding that provides noncontact sensing. The compact package series is a result of unique technology combing transfer and injection molding.

This device has a low profile.

#### **■**Features

- 1. Transmissive with phototransistor output
- 2. Highlights:
  - Compact Size
  - Narrow Gap
- 3. Key Parameters:
  - · Gap Width: 1mm
  - · Slit Width (detector side): 0.3mm
  - Package: 3.5×2.6×3.1mm
- 4. Lead free and RoHS directive compliant

#### ■Agency approvals/Compliance

1. Compliant with RoHS directive

#### ■Applications

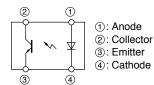
- 1. Detection of object presence or motion.
- 2. Example: printer, lens control for camera

1



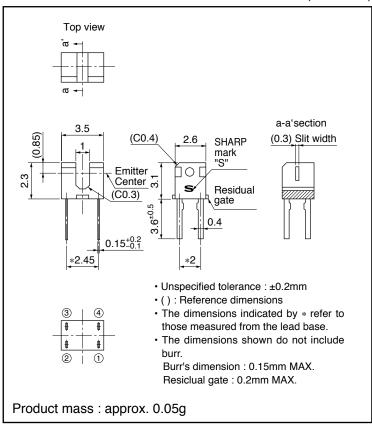
# ■ Internal Connection Diagram

Top view



#### **■** Outline Dimensions

(Unit: mm)



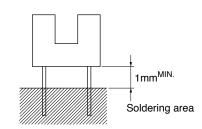
Plating material: SnCu (Cu: TYP. 2%)

Country of origin

Japan



#### ■ Absolute Maximum Ratings $(T_a=25^{\circ}C)$ Symbol Parameter Rating Unit 50 Forward current $I_{F}$ mA $V_R$ 6 V Input Reverse voltage P 75 mW Power dissipation Collector-emitter voltage $V_{\text{CEO}}$ 35 V Emitter-collector voltage $V_{ECO}$ 6 V Output Collector current 20 $I_{C}$ mACollector power dissipation $P_{C}$ 75 mW 100 Total power dissipation $P_{\text{tot}}$ mW-25 to +85 °C Operating temperature $T_{opr}$ $T_{stg}$ -40 to +100 °C Storage temperature \*1Soldering temperature $T_{sol}$ 260 °C



# **■** Electro-optical Characteristics

 $(T_a=25^{\circ}C)$ 

<u>-</u>							( -	-a <b>-</b> c - ,
Parameter			Symbol	Condition	MIN.	TYP.	MAX.	Unit
Input	Forward voltage		$V_{\rm F}$	$I_F=20mA$	_	1.2	1.4	V
	Reverse current		$I_R$	$V_R=3V$	_	_	10	μΑ
Output	Collector dark current		$I_{CEO}$	$V_{CE}=20V$	_	_	100	nA
Transfer characteristics	Collector current		$I_{C}$	$V_{CE}=5V$ , $I_F=5mA$	100	_	400	μΑ
	Collector-emitter saturation voltage		V <sub>CE(sat)</sub>	$I_F=10mA, I_C=50\mu A$	_	_	0.4	V
	Response time	Rise time	t <sub>r</sub>	$V_{CE}$ =5V, $I_{C}$ =100 $\mu$ A, $R_{L}$ =1 $k\Omega$	_	50	150	μs
		Fall time	$t_{\rm f}$		_	50	150	μs

<sup>\*1</sup> For 5s or less



Fig.1 Forward Current vs.

Ambient Temperature

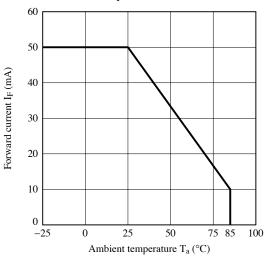


Fig.3 Forward Current vs. Forward Voltage

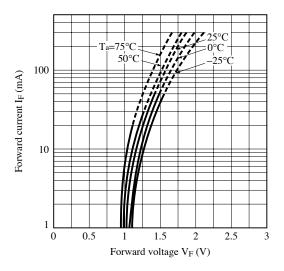


Fig.5 Collector Current vs.
Collector-emitter Voltage

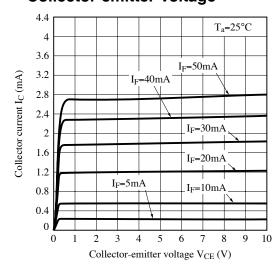


Fig.2 Power Dissipation vs. Ambient Temperature

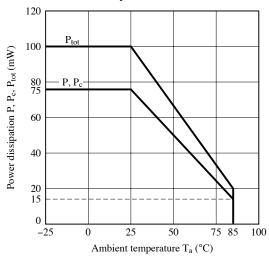


Fig.4 Collector Current vs. Forward Current

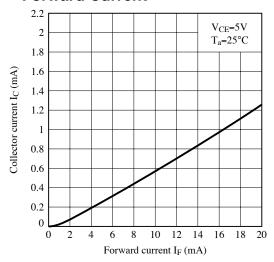


Fig.6 Relative Collector Current vs.
Ambient Temperature

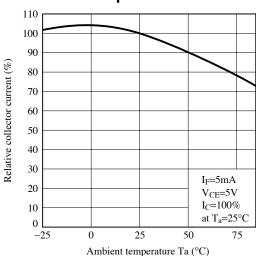




Fig.7 Collector-emitter Saturation Voltage vs. Ambient Temperature

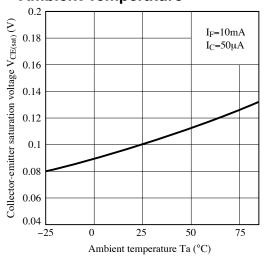


Fig.8 Collector Dark Current vs.
Ambient Temperature

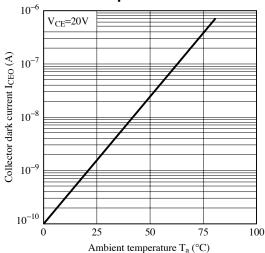


Fig.9 Response Time vs. Load Resistance

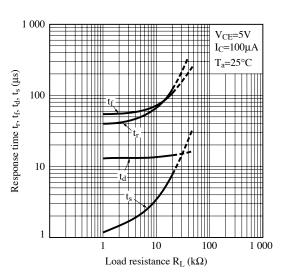


Fig.10 Test Circuit for Response Time

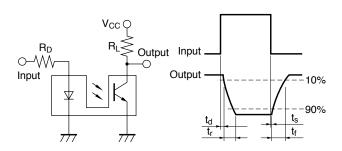


Fig.11 Detecting Position Characteristics (1)

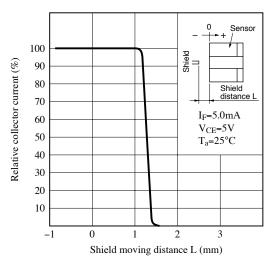
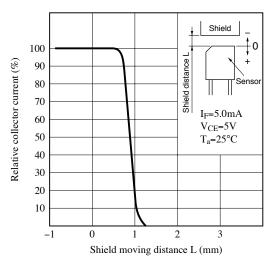


Fig.12 Detecting Position Characteristics (2)



Remarks: Please be aware that all data in the graph are just for reference and not for guarantee.



# ■ Design Considerations

### Design guide

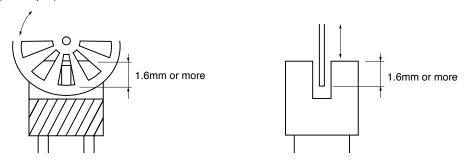
1) Prevention of detection error

To prevent photointerrupter from faulty operation caused by external light, do not set the detecting face to the external light.

2) Position of opaque board

Opaque board shall be installed at place 1.6mm or more from the top of elements.

#### (Example)



This product is not designed against irradiation and incorporates non-coherent IRED.

# Degradation

In general, the emission of the IRED used in photointerrupter will degrade over time.

In the case of long term operation, please take the general IRED degradation (50% degradation over 5 years) into the design consideration.

#### Parts

This product is assembled using the below parts.

# • Photodetector (qty.: 1)

Category	Material	Maximum Sensitivity wavelength (nm)	Sensitivity wavelength (nm)	Response time (μs)
Phototransistor	Silicon (Si)	930	700 to 1 200	20

#### • Photo emitter (qty.: 1)

Category	Material	Maximum light emitting wavelength (nm)	I/O Frequency (MHz)	
Infrared emitting diode (non-coherent)	Gallium arsenide (GaAs)	950	0.3	

#### Material

Case	Lead frame	Lead frame plating
Black polyphernylene sulfide resin (UL94 V-0)	42Alloy	SnCu plating



### ■ Manufacturing Guidelines

### Soldering Method

#### Flow Soldering:

Soldering should be completed below 260°C and within 5 s.

Please solder within one time.

Soldering area is 1mm or more away from the bottom of housing.

Please take care not to let any external force exert on lead pins.

Please don't do soldering with preheating, and please don't do soldering by reflow.

#### Hand soldering

Hand soldering should be completed within 3 s when the point of solder iron is below 350°C.

Please solder within one time.

Please don't touch the terminals directly by soldering iron.

Soldered product shall treat at normal temperature.

#### Other notice

Please test the soldering method in actual condition and make sure the soldering works fine, since the impact on the junction between the device and PCB varies depending on the cooling and soldering conditions.

### Cleaning instructions

#### Solvent cleaning:

Solvent temperature should be 45°C or below. Immersion time should be 3 minutes or less.

#### Ultrasonic cleaning:

Do not execute ultrasonic cleaning.

#### Recommended solvent materials:

Ethyl alcohol, Methyl alcohol and Isopropyl alcohol.

#### Presence of ODC

This product shall not contain the following materials.

And they are not used in the production process for this product.

Regulation substances: CFCs, Halon, Carbon tetrachloride, 1.1.1-Trichloroethane (Methylchloroform)

Specific brominated flame retardants such as the PBBOs and PBBs are not used in this product at all.

This product shall not contain the following materials banned in the RoHS Directive (2002/95/EC).

•Lead, Mercury, Cadmium, Hexavalent chromium, Polybrominated biphenyls (PBB), Polybrominated diphenyl ethers (PBDE).



# ■ Package specification

# ● Sleeve package

# Package materials

Sleeve : Polystyrene

Stopper: Styrene-Elastomer

# Package method

MAX. 100 pcs. of products shall be packaged in a sleeve. Both ends shall be closed by tabbed and tabless stoppers.

MAX. 50 sleeves in one case.



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